

100V, 3A, 95mΩ N-channel Power Trench MOSFET

JMTJ11DN10A

Features

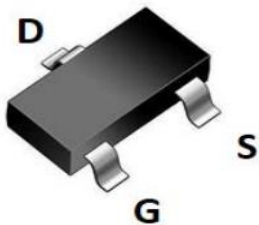
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

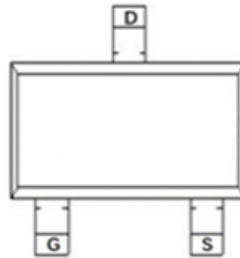
- Load Switch
- PWM Application
- Power Management

Product Summary

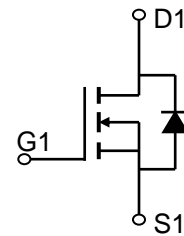
Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th)_{Typ}}$	1.6	V
$I_D (@V_{GS}=10V)$	3	A
$R_{DS(ON)_{Typ}} (@V_{GS}=10V)$	86	mΩ
$R_{DS(ON)_{Typ}} (@V_{GS}=4.5V)$	95	mΩ



SOT-23-3L Top View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTJ11DN10A	10100	3	Tape&Reel	SOT-23-3L	3000	120000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	W
		$T_A = 100^\circ\text{C}$	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	158	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	108	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

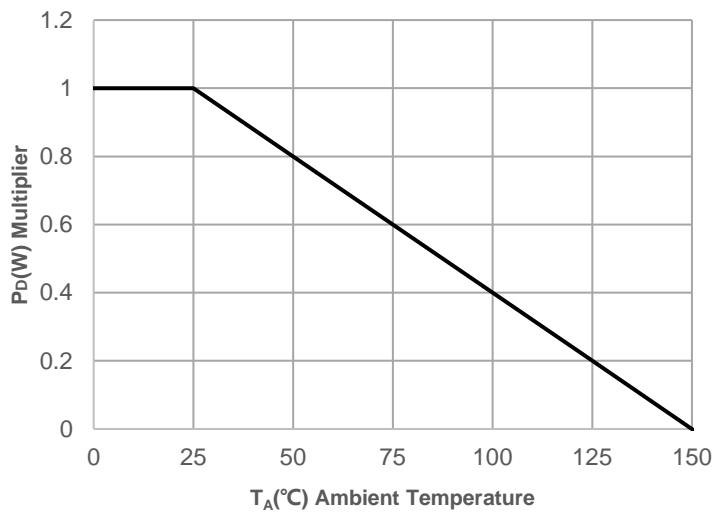
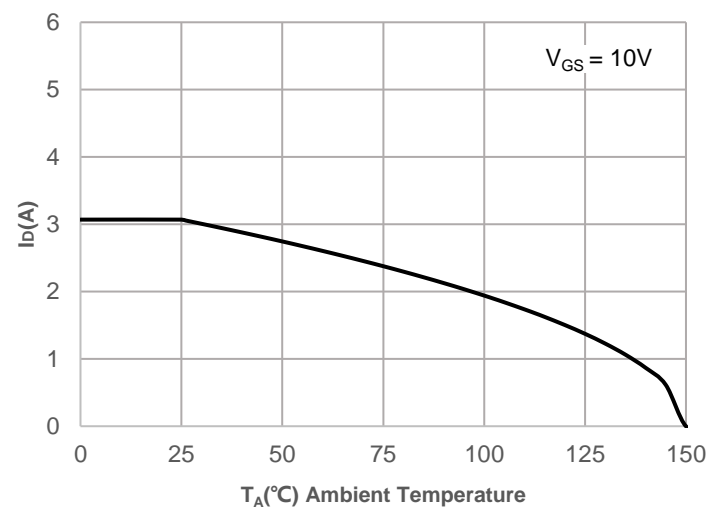
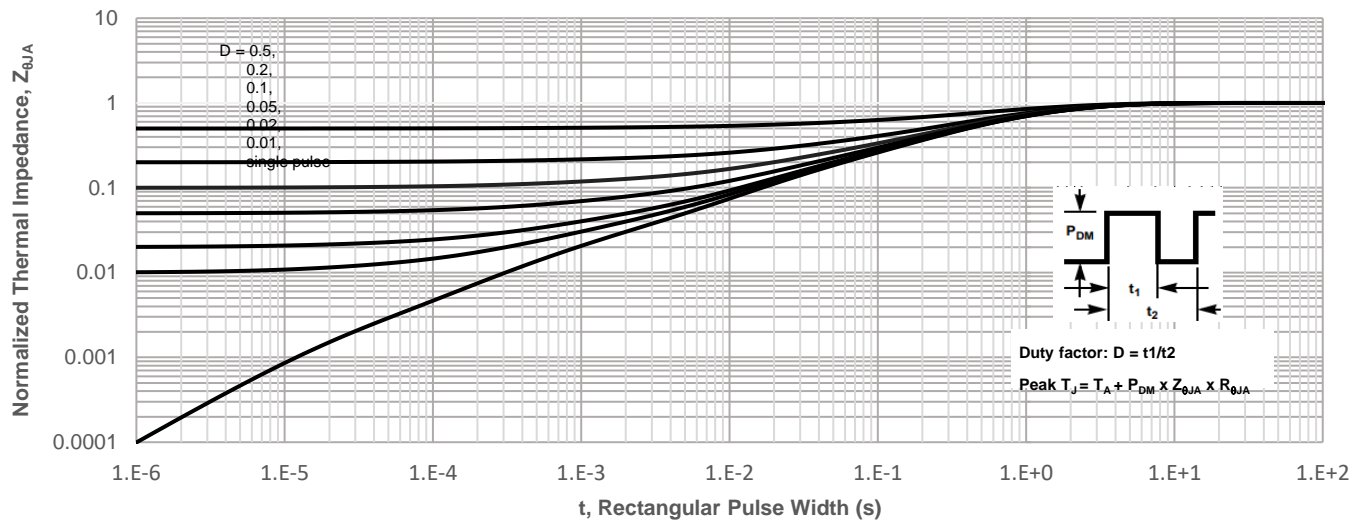
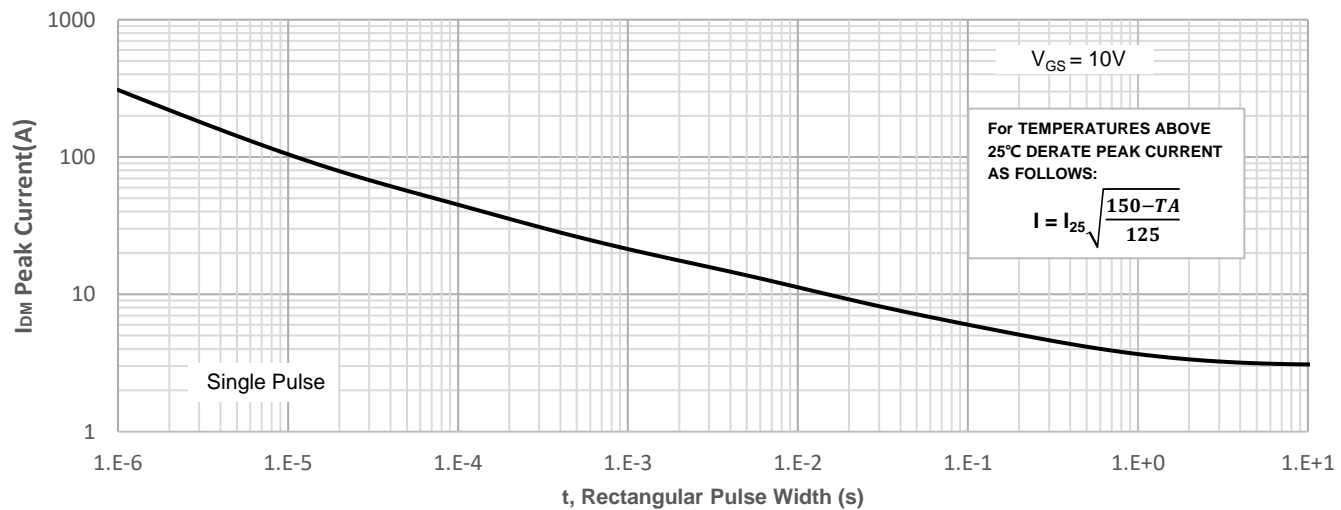
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.1	1.6	2.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 3A	-	86	112	mΩ
		V _{GS} = 4.5V, I _D = 2A	-	95	124	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	2	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	584	818	1104	pF
C _{oss}	Output Capacitance		22	31	42	pF
C _{rss}	Reverse Transfer Capacitance		18	25	34	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 5A	14	20	27	nC
Q _{gs}	Gate Source Charge		-	2.9	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	4.4	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 5A, R _{GEN} = 6.2Ω	-	5.4	-	ns
t _r	Turn-On Rise Time		-	6.9	-	ns
t _{d(off)}	Turn-Off DelayTime		-	23	-	ns
t _f	Turn-Off Fall Time		-	2.6	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	3	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	12	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 3A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 5A, di/dt = 100A/us	14	20	26	ns
Qrr	Body Diode Reverse Recovery Charge		-	18	-	nC

Notes:

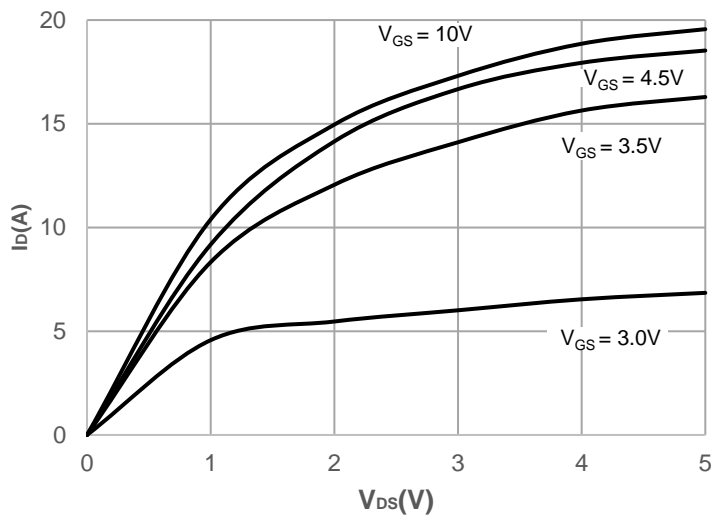
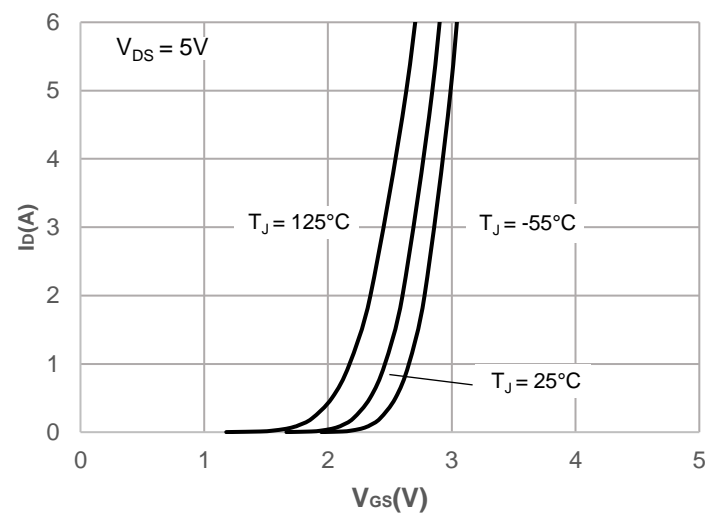
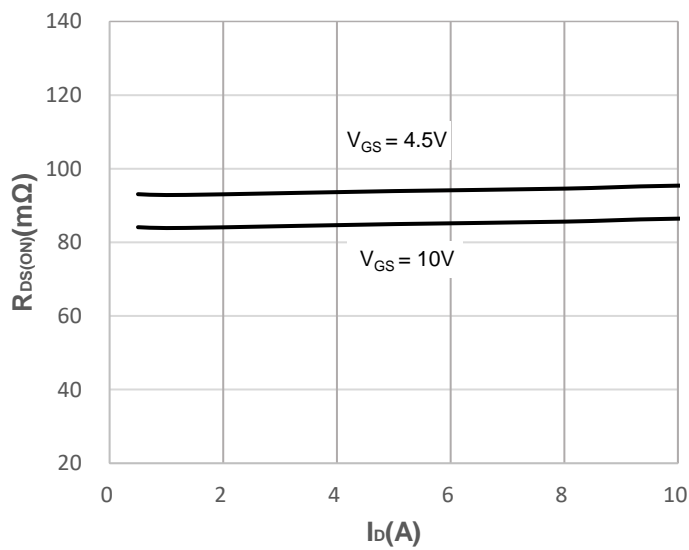
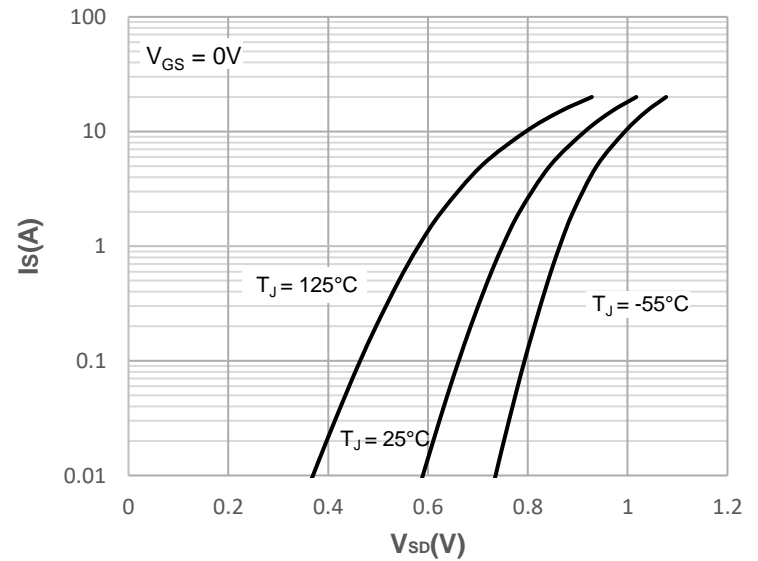
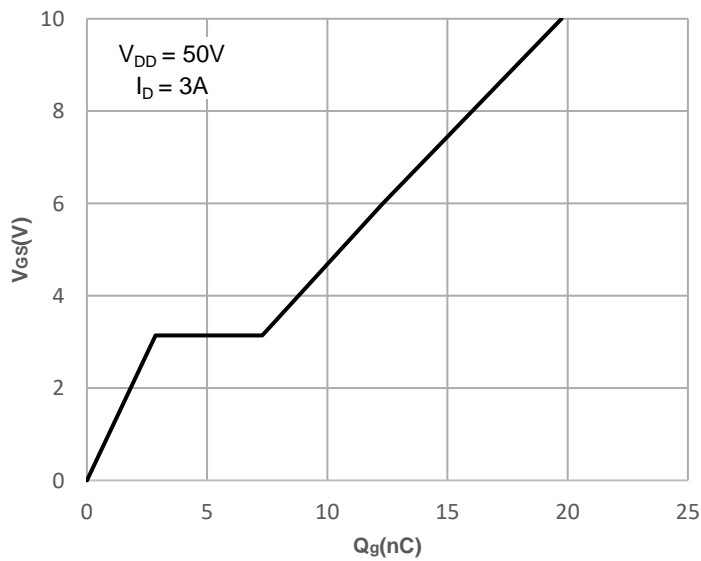
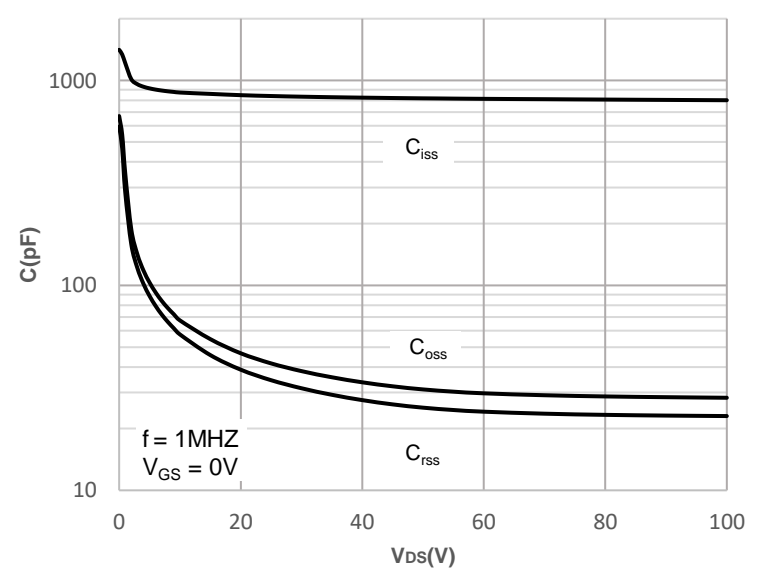
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

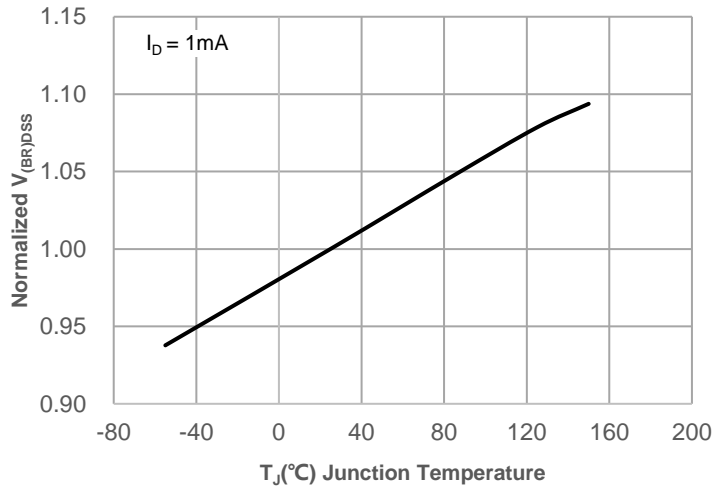


Figure 12: Normalized on Resistance vs. Junction Temperature

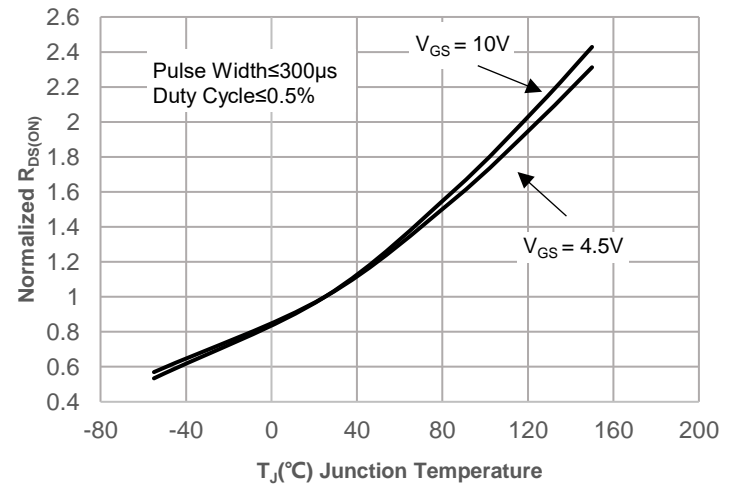


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

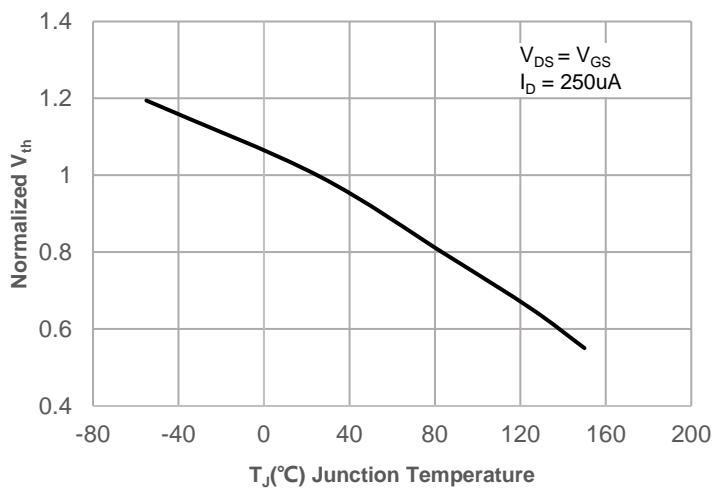


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

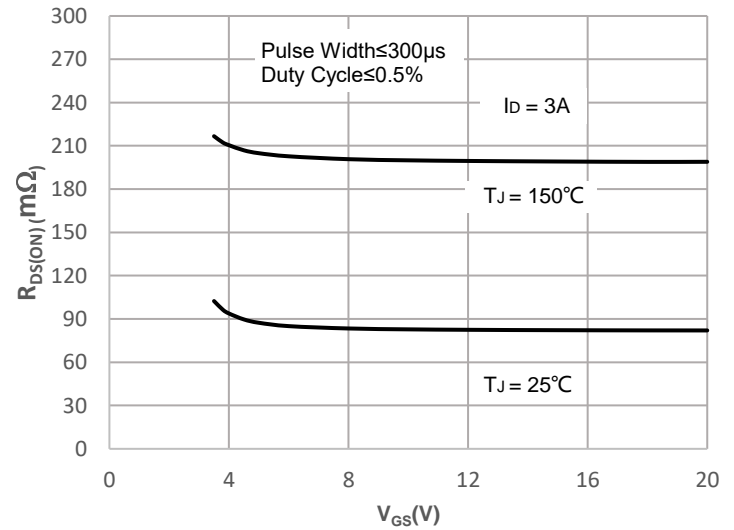
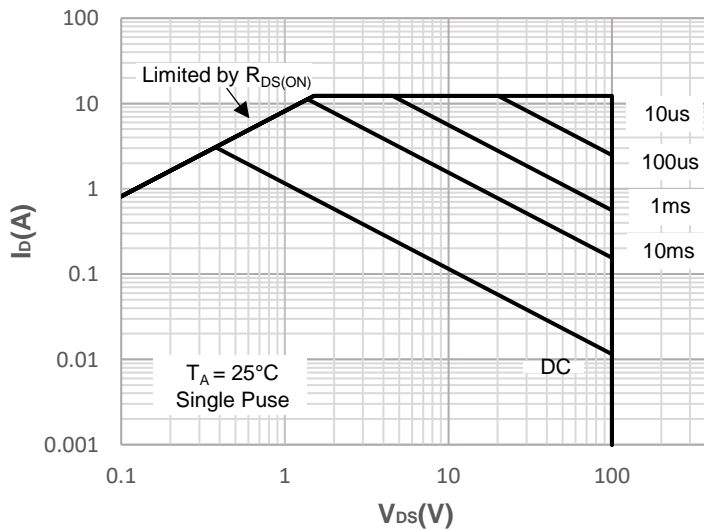


Figure 15: Maximum Safe Operating Area



Test Circuit

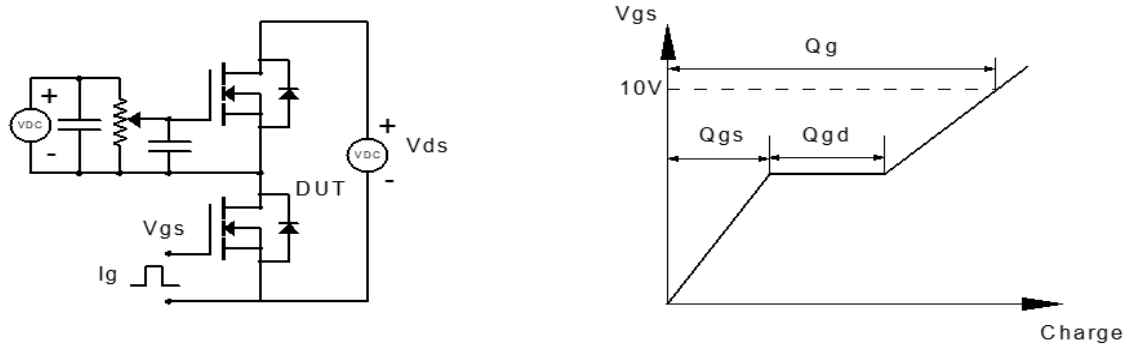


Figure 1: Gate Charge Test Circuit & Waveform

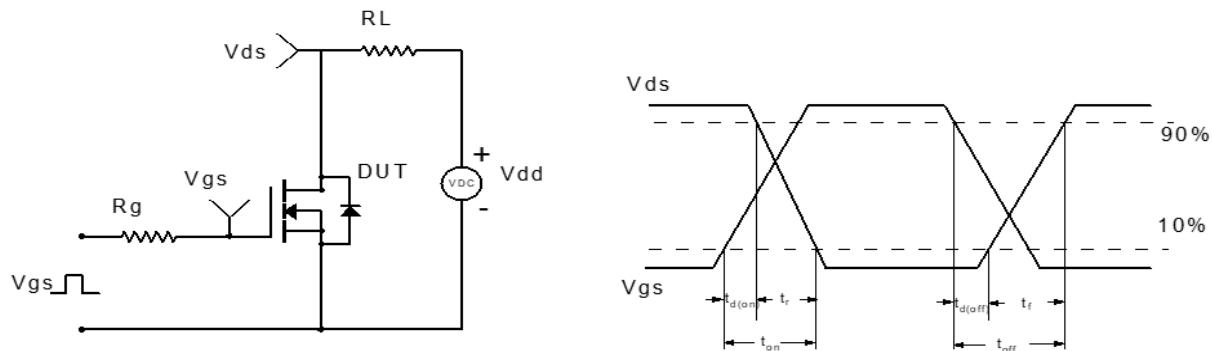


Figure 2: Resistive Switching Test Circuit & Waveform

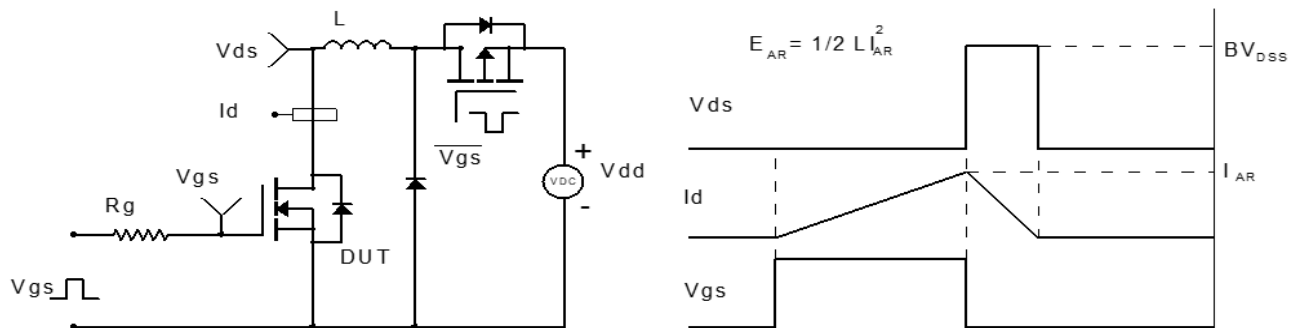


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

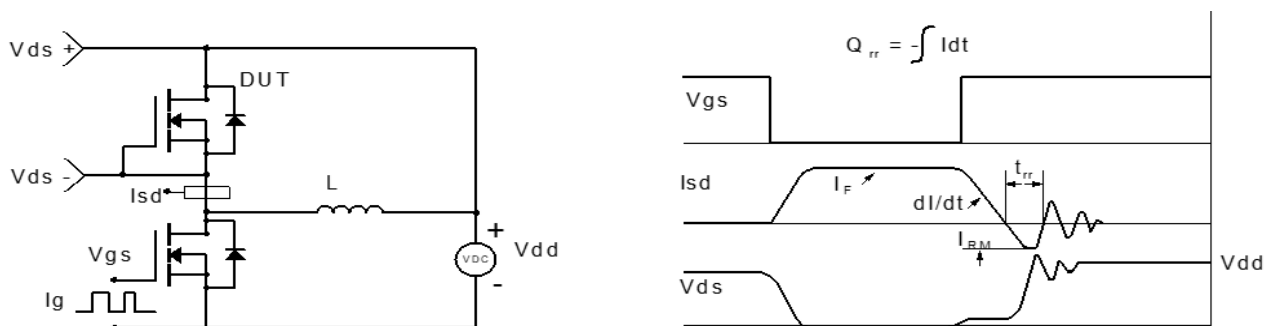
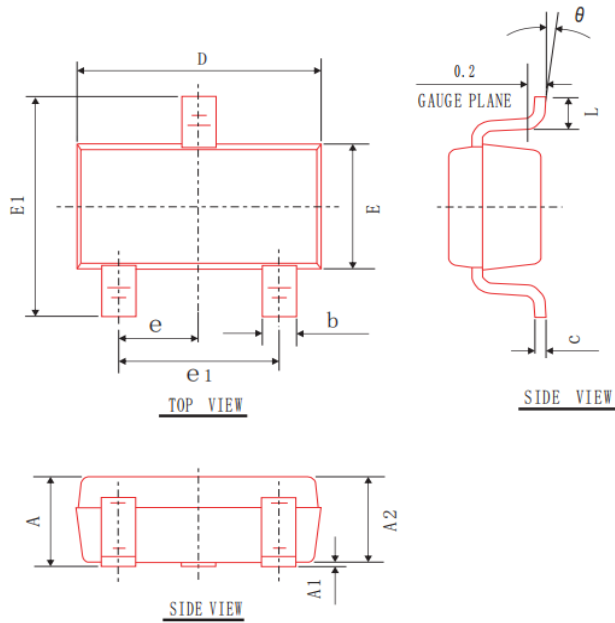


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23-3L)



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	—	—	1.30
A1	0.00	0.05	0.10
A2	1.00	1.10	1.20
b	0.30	0.40	0.50
c	0.119	0.127	0.135
e1	1.80	1.90	2.00
D	2.80	2.90	3.00
E	1.50	1.60	1.70
E1	2.60	2.80	3.00
L	0.30	0.45	0.60
θ	0°	4°	8°
e	0.95BSC		

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